

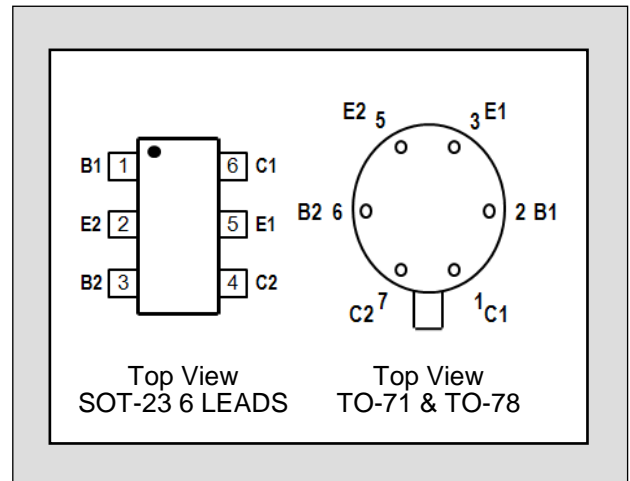
LINEAR SYSTEMS

Twenty-Five Years Of Quality Through Innovation

LS350 LS351 LS352

MONOLITHIC DUAL PNP TRANSISTORS

FEATURES		
HIGH GAIN	h_{FE} 200 @ 10 μ A - 1mA	
TIGHT V_{BE} MATCHING	$ V_{BE1} - V_{BE2} = 0.2\text{mV TYP.}$	
HIGH f_T	275 MHz TYP. @ 1mA	
ABSOLUTE MAXIMUM RATINGS NOTE 1		
@ 25 °C (unless otherwise stated)		
I_C	Collector Current	10mA
Maximum Temperatures		
Storage Temperature	-55° to +150°C	
Operating Junction Temperature	+150°C	
Maximum Power Dissipation	ONE SIDE	BOTH SIDES
Device Dissipation @ Free Air	250mW	500mW
Linear Derating Factor	2.3mW/°C	4.3mW/°C



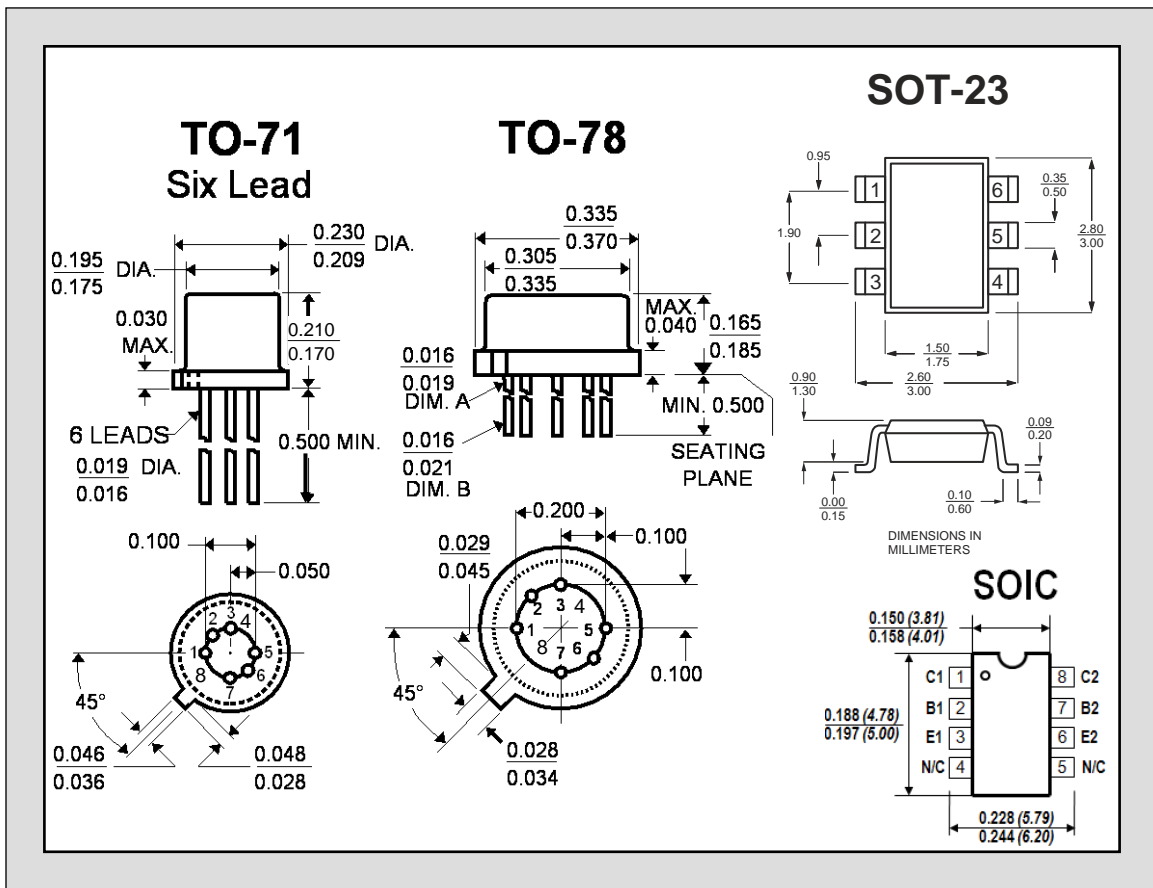
ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	LS350	LS351	LS352		UNITS	CONDITIONS
BV_{CBO}	Collector to Base Voltage	25	45	60	MIN.	V	$I_C = 10\mu\text{A}$ $I_E = 0$
BV_{CEO}	Collector to Emitter Voltage	25	45	60	MIN.	V	$I_C = 1\text{mA}$ $I_B = 0$
BV_{EBO}	Emitter to Base Voltage	6.0	6.0	6.0	MIN.	V	$I_E = 10\mu\text{A}$ $I_C = 0$ NOTE 2
BV_{CCO}	Collector to Collector Voltage	± 25	± 45	± 80	MIN.	V	$I_C = \pm 1\mu\text{A}$ $I_E = 0 = I_B = 0$
h_{FE}	DC Current Gain	100	150	200	MIN.		$I_C = 10\mu\text{A}$ $V_{CE} = 5\text{V}$
			600	600	MAX.		
h_{FE}	DC Current Gain	100	150	200	MIN.		$I_C = 100\mu\text{A}$ $V_{CE} = 5\text{V}$
			600	600	MAX.		
h_{FE}	DC Current Gain	100	150	200	MIN.		$I_C = 1\text{mA}$, $V_{CE} = 5\text{V}$
$V_{CE(SAT)}$	Collector Saturation Voltage	0.5	0.5	0.5	MAX.	V	$I_C = 1\text{mA}$ $I_B = 0.1\text{mA}$
I_{CBO}	Collector Cutoff Current	0.2	0.2	0.2	MAX.	nA	$I_E = 0$ $V_{CB} = \text{NOTE 3}$
I_{EBO}	Emitter Cutoff Current	0.2	0.2	0.2	MAX.	nA	$I_C = 0$ $V_{EB} = 3\text{V}$
C_{OBO}	Output Capacitance	2	2	2	MAX.	pF	$I_E = 0$ $V_{CB} = 5\text{V}$
C_{C1C2}	Collector to Collector Capacitance	2	2	2	MAX.	pF	$V_{CC} = 0$
I_{C1C2}	Collector to Collector Leakage Current	1.0	1.0	1.0	MAX.	μA	$V_{CC} = \text{NOTE 4}$
f_T	Current Gain Bandwidth Product	200	200	200	MIN.	MHz	$I_C = 1\text{mA}$ $V_{CE} = 5\text{V}$
NF	Narrow Band Noise Figure	3	3	3	MAX.	dB	$I_C = 100\mu\text{A}$ $V_{CE} = 5\text{V}$ $BW = 200\text{Hz}$ $R_G = 10\text{K}$ $f = 1\text{KHz}$

**LS350
SOT-23**

MATCHING CHARACTERISTICS

SYMBOL	CHARACTERISTIC	LS350	LS351	LS352		UNITS	CONDITIONS
$ V_{BE1} - V_{BE2} $	Base Emitter Voltage Differential	1	0.4	0.2	TYP.	mV	$I_C = 10 \mu A$ $V_{CE} = 5V$
		5	1.0	0.5	MAX.	mV	
$ d(V_{BE1} - V_{BE2})/dT $	Base Emitter Voltage Differential Change with Temperature	2	1	0.5	TYP.	$\mu V/^\circ C$	$I_C = 10 \mu A$ $V_{CE} = 5V$
		20	10	2	MAX.	$\mu V/^\circ C$	$T_A = -55^\circ C$ to $+125^\circ C$
$ I_{B1} - I_{B2} $	Base Current Differential		5	5	MAX.	nA	$I_C = 10 \mu A$ $V_{CE} = 5V$
$ d(I_{B1} - I_{B2})/dT $	Base Current Differential Change with Temperature		0.5	0.3	MAX.	$nA/^\circ C$	$I_C = 10 \mu A$, $V_{CE} = 5V$ $T_A = -55^\circ C$ to $+125^\circ C$
h_{FE1}/h_{FE2}	DC Current Gain Differential	10	5	5	TYP.	%	$I_C = 10 \mu A$ $V_{CE} = 5V$



NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired
2. The reverse base-to-emitter voltage must never exceed 6.0 volts; the reverse base-to-emitter current must never exceed 10 μA .
3. For LS350: $V_{CB}=20V$; for LS351 & LS352: $V_{CB}=30V$.
4. For LS351: $V_{CC}=\pm 45V$; for LS352: $V_{CC}=\pm 80V$; for LS350: $V_{CC}=\pm 25V$.

Linear Integrated Systems (LIS) is a 25-year-old, third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company President John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, co-founder and vice president of R&D at Intersil, and founder/president of Micro Power Systems.